

HAT2134H

Silicon N Channel Power MOS FET Power Switching

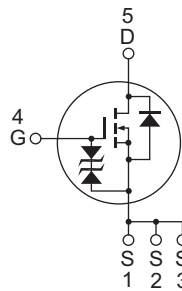
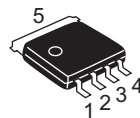
REJ03G1190-0300
(Previous: ADE-208-1578A)
Rev.3.00
Sep 07, 2005

Features

- Capable of 4.5 V gate drive
- Low drive current
- High density mounting
- Low on-resistance
 $R_{DS(on)} = 2.3 \text{ m}\Omega$ typ. (at $V_{GS} = 10 \text{ V}$)

Outline

RENESAS Package code: PTZZ0005DA-A
(Package name: LFAK)



1, 2, 3 Source
4 Gate
5 Drain

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Drain to source voltage	V_{DS}	20	V
Gate to source voltage	V_{GS}	±20	V
Drain current	I_D	60	A
Drain peak current	$I_{D(pulse)}$ ^{Note 1}	240	A
Body-drain diode reverse drain current	I_{DR}	60	A
Avalanche current	I_{AP} ^{Note 3}	20	A
Avalanche energy	E_{AR} ^{Note 3}	40	mJ
Channel dissipation	P_{ch} ^{Note 2}	30	W
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Notes: 1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$
 2. $T_c = 25^\circ C$
 3. Value at $T_{ch} = 25^\circ C$, $R_g \geq 50 \Omega$

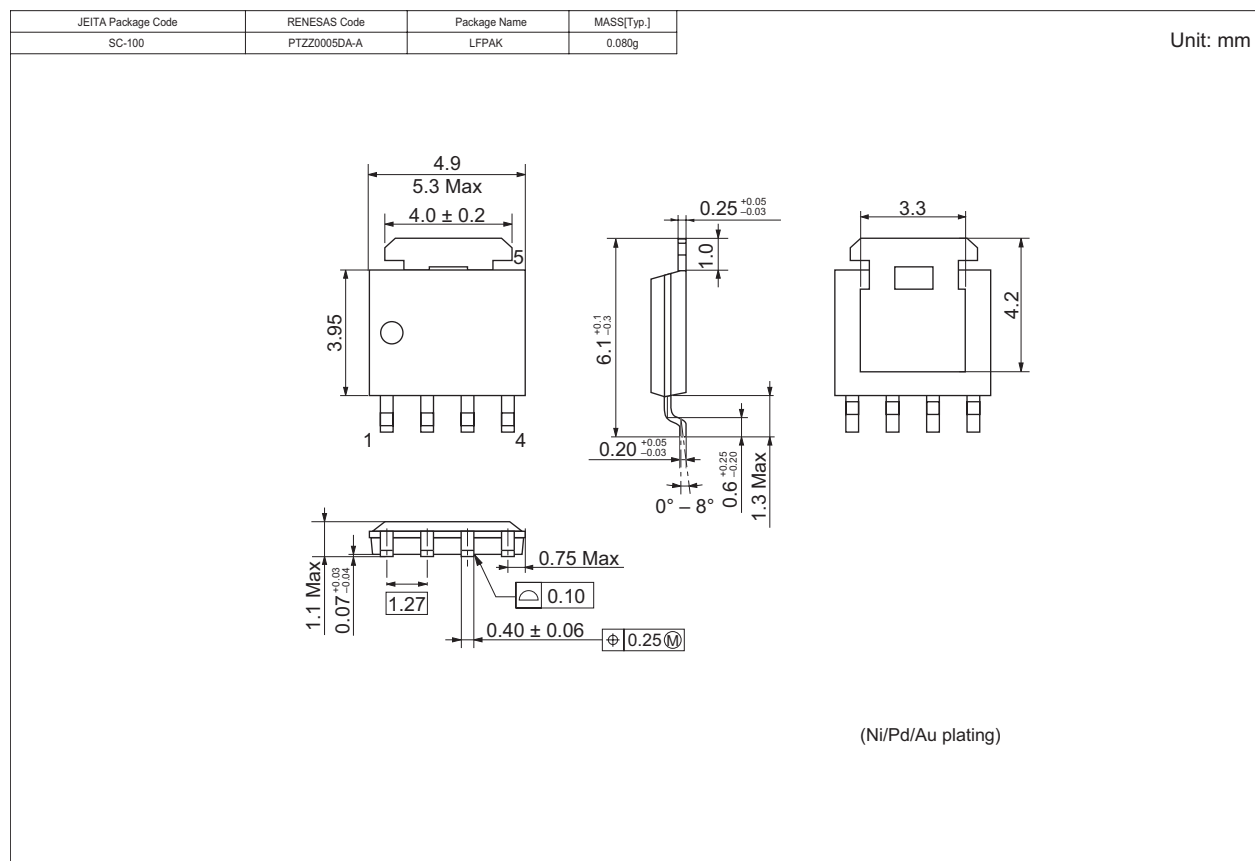
Electrical Characteristics

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DS}$	20	—	—	V	$I_D = 10 \text{ mA}$, $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GS}$	±20	—	—	V	$I_G = \pm 100 \mu A$, $V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	±10	μA	$V_{GS} = \pm 16 \text{ V}$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	1	μA	$V_{DS} = 20 \text{ V}$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.5	V	$V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$
Static drain to source on state resistance	$R_{DS(on)}$	—	2.3	2.9	mΩ	$I_D = 30 \text{ A}$, $V_{GS} = 10 \text{ V}$ ^{Note 4}
	$R_{DS(on)}$	—	4.0	5.8	mΩ	$I_D = 30 \text{ A}$, $V_{GS} = 4.5 \text{ V}$ ^{Note 4}
Forward transfer admittance	$ y_{fs} $	51	85	—	S	$I_D = 30 \text{ A}$, $V_{DS} = 10 \text{ V}$ ^{Note 4}
Input capacitance	C_{iss}	—	4500	—	pF	$V_{DS} = 10 \text{ V}$
Output capacitance	C_{oss}	—	1200	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	560	—	pF	$f = 1 \text{ MHz}$
Total gate charge	Q_g	—	70	—	nC	$V_{DD} = 10 \text{ V}$
Gate to source charge	Q_{gs}	—	15	—	nC	$V_{GS} = 10 \text{ V}$
Gate to drain charge	Q_{gd}	—	11	—	nC	$I_D = 60 \text{ A}$
Turn-on delay time	$t_{d(on)}$	—	20	—	ns	$V_{GS} = 10 \text{ V}$, $I_D = 30 \text{ A}$
Rise time	t_r	—	60	—	ns	$V_{DD} \approx 10 \text{ V}$
Turn-off delay time	$t_{d(off)}$	—	85	—	ns	$R_L = 0.33 \Omega$
Fall time	t_f	—	17	—	ns	$R_g = 4.7 \Omega$
Body-drain diode forward voltage	V_{DF}	—	0.85	1.10	V	$I_F = 60 \text{ A}$, $V_{GS} = 0$ ^{Note 4}
Body-drain diode reverse recovery time	t_{rr}	—	50	—	ns	$I_F = 60 \text{ A}$, $V_{GS} = 0$ $di_F/dt = 50 \text{ A}/\mu s$

Note: 4. Pulse test

Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
HAT2134H-EL-E	2500 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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